

Attorney Docket No.: 0150114D

In the Claims:**Claims 1-13 (canceled).**

Claim 14 (currently amended): A method for fabricating a composite capacitor in a semiconductor die, said method comprising steps of:

- depositing a lower interconnect metal layer;
- forming an upper electrode of a lower capacitor over said lower interconnect metal layer;
- patterning said lower interconnect metal layer to form a lower electrode of said lower capacitor;
- depositing an interlayer dielectric layer over said upper electrode and said lower electrode of said lower capacitor;
- depositing an upper interconnect metal layer over said interlayer dielectric layer;
- forming an upper electrode of an upper capacitor over said upper interconnect metal layer;
- patterning said upper interconnect metal layer to form a lower electrode of said upper capacitor;
- wherein said lower electrode of said lower capacitor is electrically connected to said upper electrode of said upper capacitor so as to couple said lower capacitor and said upper capacitor in a parallel configuration.

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Claim 15 (original): The method of claim 14 further comprising a step of connecting said upper electrode of said lower capacitor to said lower electrode of said upper capacitor by at least one via.

Claim 16 (original): The method of claim 14 further comprising a step of connecting said lower electrode of said lower capacitor to said upper electrode of said upper capacitor by at least one via.

Claim 17 (original): The method of claim 14 further comprising a step of forming a high-k dielectric between said lower and upper electrodes of said lower capacitor.

Claim 18 (original): The method of claim 17 wherein said high-k dielectric is selected from the group consisting of silicon oxide, silicon nitride, tantalum pentoxide, aluminum oxide, hafnium oxide, zirconium oxide, zirconium aluminum silicate, hafnium silicate, and hafnium aluminum silicate.

Claim 19 (original): The method of claim 14 further comprising a step of forming a high-k dielectric between said lower and upper electrodes of said upper capacitor.

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Claim 20 (original): The method of claim 19 wherein said high-k dielectric is selected from the group consisting of silicon oxide, silicon nitride, tantalum pentoxide, aluminum oxide, hafnium oxide, zirconium oxide, zirconium aluminum silicate, hafnium silicate, and hafnium aluminum silicate.

Claim 21 (original): The method of claim 14 wherein said upper electrode of said lower capacitor and said upper electrode of said upper capacitor comprise metal selected from the group consisting of titanium nitride and tantalum nitride.

Claim 22 (original): The method of claim 14 wherein said upper electrode of said lower capacitor and said upper electrode of said upper capacitor are fabricated utilizing a common mask.